

**REMARKS**

Claims 1-10 and 20-47 are canceled, leaving claims 11-19 pending in the application. Applicant requests substantive examination of pending claims 11-19.

Respectfully submitted,

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By:   
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TOP SECRET - DTI 0802

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

priority Application Serial No. .... 09/633,556  
priority Filing Date ..... August 7, 2000  
Inventor ..... Gurtej S. Sandhu et al.  
Assignee ..... Micron Technology, Inc.  
priority Group Art Unit ..... 2813  
priority Examiner ..... Laura M. Schillinger  
Attorney's Docket No. ..... MI22-1896  
Title: Methods of Forming a Nitrogen Enriched Region

**VERSION WITH MARKINGS TO SHOW CHANGES MADE**  
**ACCOMPANYING PRELIMINARY AMENDMENT**

**In the Specification**

The replacement specification paragraphs incorporate the following amendments. Underlines indicate insertions and ~~strikeouts~~ indicate deletions.

The title is amended as follows: ~~Transistor Structures, Methods of Incorporating Nitrogen into Silicon Oxide-Containing Layers; and Methods of Forming Transistors~~ Methods of Forming a Nitrogen Enriched Region

The following is inserted on p. 1 before the "Technical Field" section,

**CROSS REFERENCE TO RELATED APPLICATION**

This patent resulted from a divisional application of U.S. Patent Application Serial No. 09/633,556, which was filed on August 7, 2000.

**In the Claims**

Claims 1-10 and 20-47 are canceled.

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